

General Description

The CMSA018N025 is designed to provide a high efficiency synchronous buck power stage with optimal layout and board space utilization. This device is well suited for use in compact DC/DC converter applications.

Features

- Low ON-resistance
- 100% EAS Guaranteed
- Surface Mount Package
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	25	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	100	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	70	A
I_{DM}	Pulsed Drain Current	400	A
EAS	Single Pulse Avalanche Energy ¹	242	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	83	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(Device on PCB)	---	60	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-case	---	1.5	$^\circ\text{C}/\text{W}$

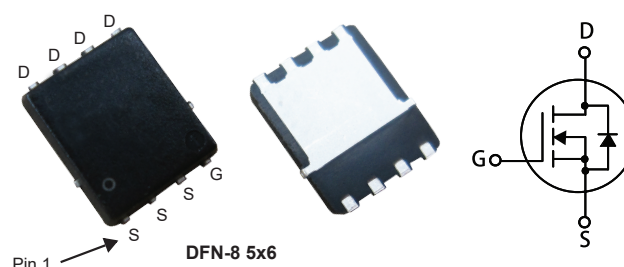
Product Summary

BVDSS	RDSON	ID
25V	1.8m Ω	100A

Applications

- Load switch, battery switch in portable devices

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA018N025	DFN-8 5x6	018N025

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	25	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=40A$	---	1.5	1.8	m Ω
		$V_{GS}=4.5V$, $I_D=30A$	---	2	2.6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D = 250\mu A$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	---	53	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3	---	Ω
Q_g	Total Gate Charge	$V_{DD}=15V$, $I_D=30A$ $V_{GS}=0$ to $4.5V$	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	7	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=1.6\Omega$ $I_D=30A$	---	6	---	ns
T_r	Rise Time		---	8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2500	---	pF
C_{oss}	Output Capacitance		---	1500	---	
C_{rss}	Reverse Transfer Capacitance		---	160	---	

Diode Characteristics

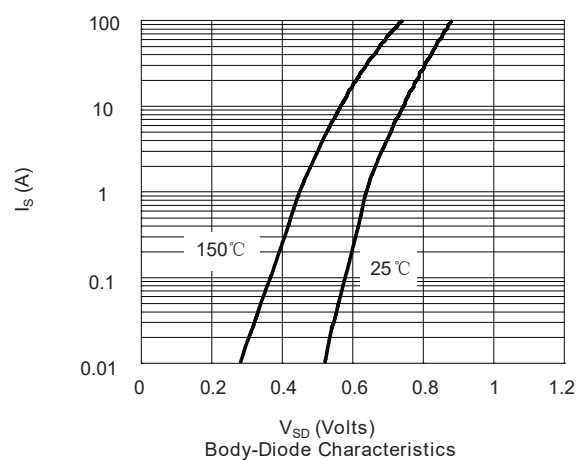
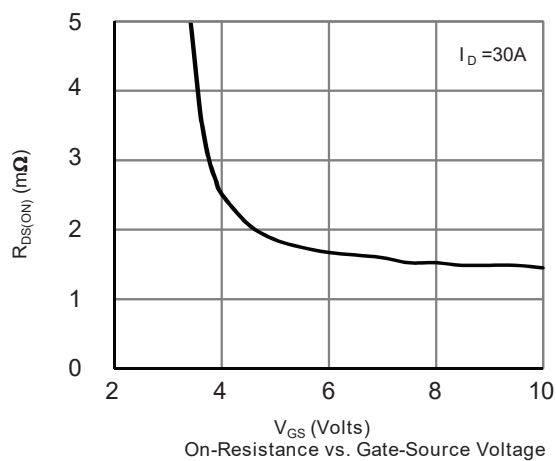
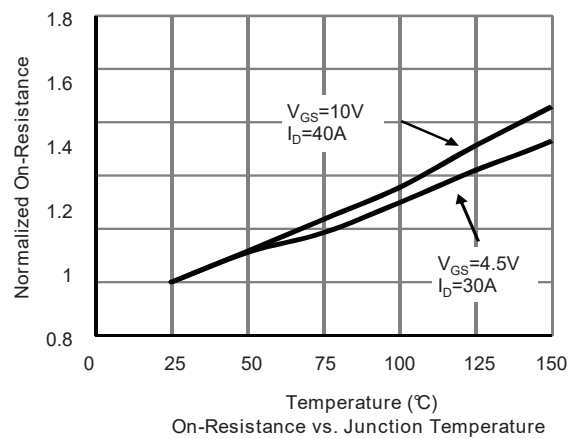
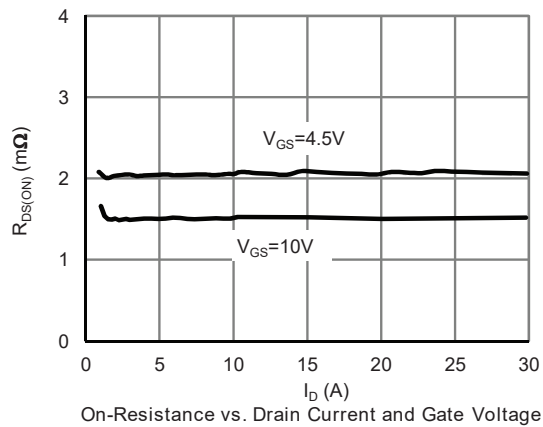
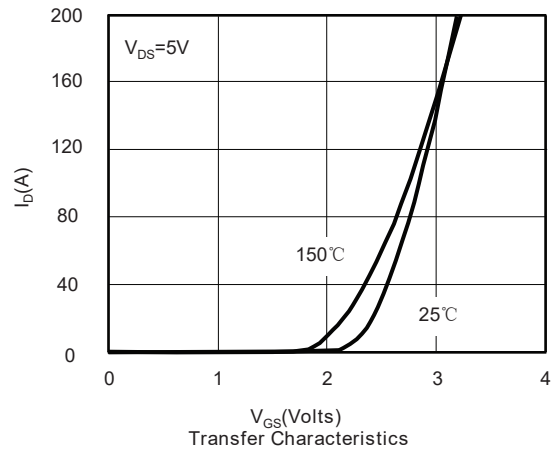
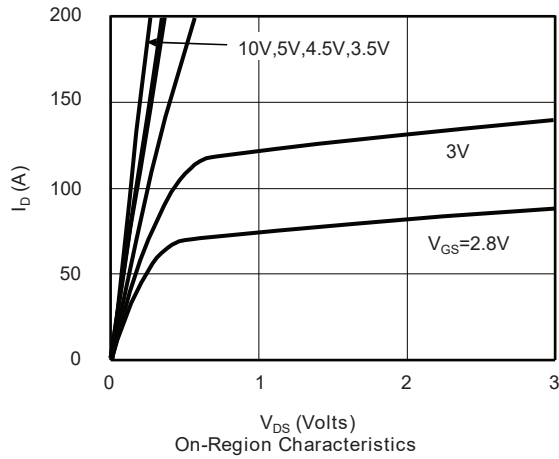
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	100	A
$I_{S,pulse}$	Diode pulse current		---	---	400	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$, $T_J=25^{\circ}\text{C}$	---	0.79	1.2	V

Notes:

1.The EAS data shows Max. rating .The test condition is $V_{DS}=20V$, $V_{GS}=10V$, $L=1\text{mH}$, $I_{AS}=22A$.

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 Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics



Typical Characteristics

